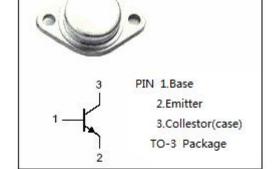


ISC Silicon NPN Power Transistor

2SC1195

DESCRIPTION

- With TO-3 Package
- · High voltage
- · Wide area of safe operation
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

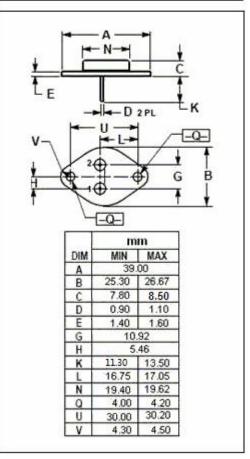


APPLICATIONS

· For power amplifier applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	200	V
V _{CEO}	Collector-Emitter Voltage	200	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current-Continuous	2.5	А
Pc	Collector Power Dissipation	100	W
TJ	Junction Temperature	150	$^{\circ}$
T _{stg}	Storage Temperature Range	-55~150	$^{\circ}$





ISC Silicon NPN Power Transistor

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ELECTRICAL CHARACTERISTICS

 T_c =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =2.5A; I _B = 0.5A			1.5	V
V _{BE} (ON)	Base-Emitter On Voltage	I _C =1.0A; V _{CE} = 5V			1.5	V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 25mA; I _B = 0	200			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	5			V
h _{FE}	DC Current Gain	I _C =1.0A; V _{CE} = 5V	30		150	



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